

NPN SILICON RF TRANSISTOR

DESCRIPTION:

The **ASI MRF905** is Designed for General Purpose Oscillator Applications.

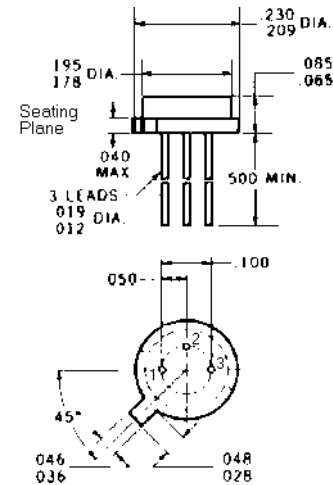
FEATURES:

- $V_{CC} = 20\text{ V}$
- **Omnigold™** Metalization System
- Collector Connected to Case

MAXIMUM RATINGS

I_C	150 mA
V_{CB}	35 V
P_{DISS}	4.0 W @ $T_C = 100\text{ }^\circ\text{C}$
T_J	-65 $^\circ\text{C}$ to +200 $^\circ\text{C}$
T_{STG}	-65 $^\circ\text{C}$ to +200 $^\circ\text{C}$
θ_{JC}	25 $^\circ\text{C/W}$

PACKAGE STYLE TO-46



1 = EMITTER 2 = BASE 3 = COLLECTOR

CHARACTERISTICS $T_C = 25\text{ }^\circ\text{C}$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 10\text{ mA}$			20			V
BV_{CBO}	$I_C = 100\text{ }\mu\text{A}$			35			V
BV_{EBO}	$I_E = 100\text{ }\mu\text{A}$			3.5			V
I_{CBO}	$V_{CB} = 20\text{ V}$					100	μA
h_{FE}	$V_{CE} = 10\text{ V}$	$I_C = 100\text{ mA}$		20		150	---
C_{OB}	$V_{CB} = 20\text{ V}$	$f = 1.0\text{ MHz}$				5.0	pF
f_T	$V_{CE} = 10\text{ V}$	$I_C = 100\text{ mA}$	$f = 200\text{ MHz}$		2500		MHz
P_{OUT}	$V_E = 20\text{ V}$	$I_E = 110\text{ mA}$	$f = 1.68\text{ GHz}$	400	500		mW